

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application No. : TO BE ASSIGNED, A DIVISIONAL OF APPLICATION NO. 10/213,091  
FILED AUGUST 7, 2002  
Applicant : JEWELL, JACK L.  
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Title : A LIGHT EMITTING DEVICE  
  
Art Unit : 2828  
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Atty Docket No. : PICO-0047-1

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

Pursuant to 37 C.F.R. §§ 1.51(b), 1.56, 1.97 and 1.98, this Information Disclosure Statement is submitted in the above-identified patent application, which claims the priority date of August 7, 2002, U.S. Patent Application No. 10/213,091. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each U.S. and foreign patent, or each publication or portion thereof listed or herein identified, is submitted herewith, except that a copy of any U.S. patent application identified herein or any patent, publication or other information listed herein cited or submitted in a prior application relied upon for an earlier filing date and identified below, is not submitted herewith.

This Information Disclosure Statement is submitted within three months of (i) the filing date of the above-identified U.S. National Patent application, or (ii) the date of entry into the U.S. National Stage of the above-identified International Application, or (iii) the date of entry into the U.S. National Stage of the International Application that has been assigned the above-identified U.S. Patent application number, whichever applies.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Please charge any additional fees or credit any overpayments in connection with this paper to **Deposit Account No. 10-0233 PICO-0047-1.**

Respectfully submitted,



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<b>Form PTO 1449</b>  <b>U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>  <b>Information Disclosure Statement by Applicant</b>	<b>ATTY. DOCKET NUMBER</b> <b>PICO-0042-1</b>	<b>SERIAL NUMBER</b> <b>10/213,091</b>
	<b>APPLICANT</b> <b>JEWELL, Jack L.</b>	
	<b>FILING DATE</b> <b>August 7, 2002</b>	<b>GROUP</b> <b>2828</b>

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	4,216,036	Aug., 1980	Tsang			
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							YES	NO

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<p><b>EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant</b></p>	